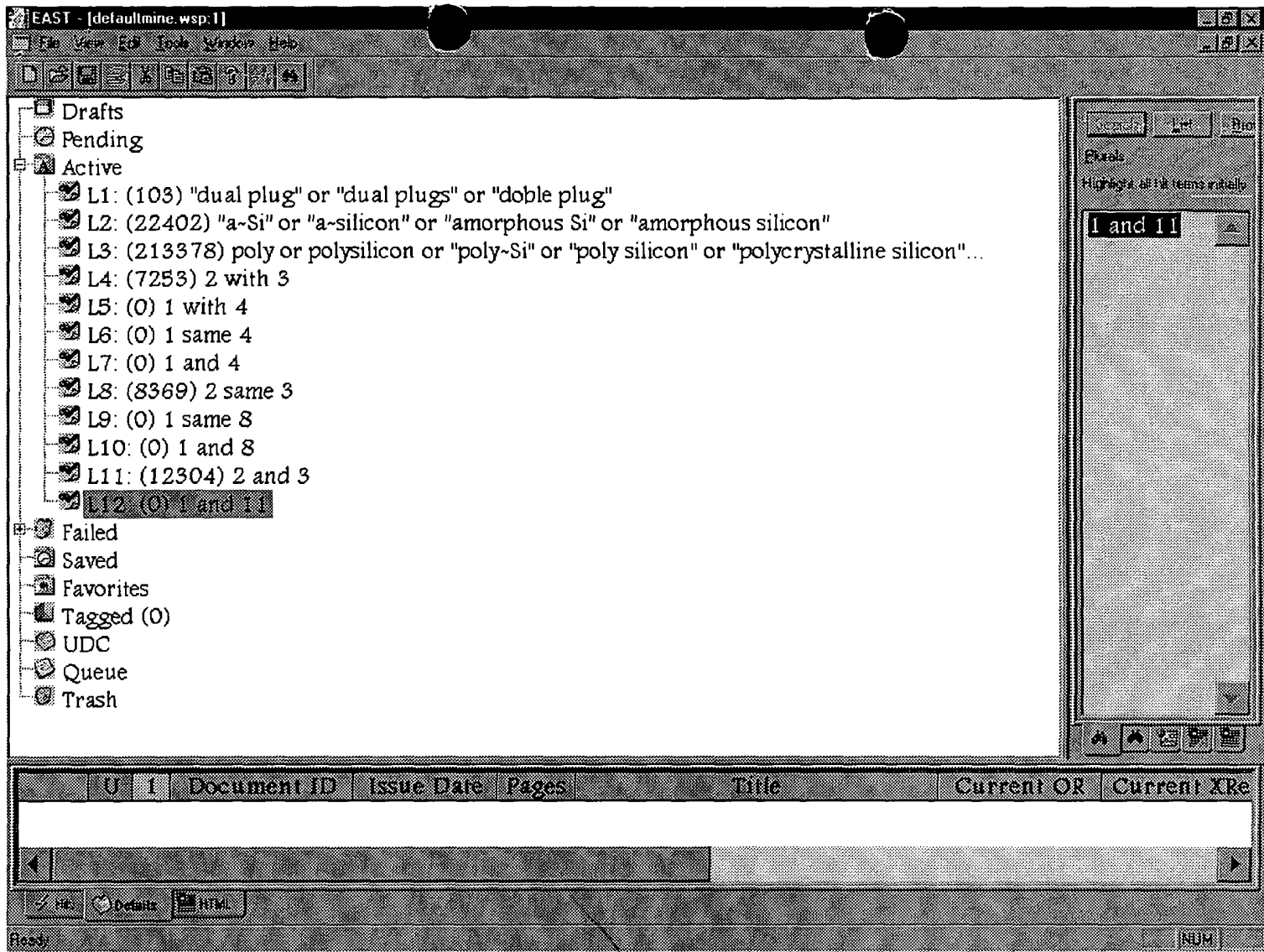


L Number	Hits	Search Text	DB	Time stamp
1	2151855	hole or window or opening or trench or via or groove or cavity or recess or aperture	USPAT; US-PGPUB	2002/11/06 21:04
2	22402	"a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon"	USPAT; US-PGPUB	2002/11/06 21:05
3	213378	polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si"	USPAT; US-PGPUB	2002/11/06 21:08
4	7253	("a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon" ) with (polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si")	USPAT; US-PGPUB	2002/11/06 21:08
5	429	(hole or window or opening or trench or via or groove or cavity or recess or aperture) with (("a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon" ) with (polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si"))	USPAT; US-PGPUB	2002/11/06 21:09
6	58074	438/\$7.ccls.	USPAT; US-PGPUB	2002/11/06 21:09
7	275	((hole or window or opening or trench or via or groove or cavity or recess or aperture) with (("a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon" ) with (polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si")))) and 438/\$7.ccls.	USPAT; US-PGPUB	2002/11/06 21:10
8	12693	LPCVD or "low pressure chemical vapor deposition" or "low pressure CVD" or "low pressure thermal CVD"	USPAT; US-PGPUB	2002/11/06 21:12
9	257	UHVCVD or "ultra high vacuum chemical vapor deposition" or "ultra-high vacuum chemical vapor deposition" or "ultra high vacuum CVD" or "ultra-high vacuum CVD"	USPAT; US-PGPUB	2002/11/06 21:15
10	282	((("a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon" ) with (polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si")) with (LPCVD or "low pressure chemical vapor deposition" or "low pressure CVD" or "low pressure thermal CVD"))	USPAT; US-PGPUB	2002/11/06 21:15
11	21	(hole or window or opening or trench or via or groove or cavity or recess or aperture) with (((("a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon" ) with (polysilicon or poly or "poly-Si" or "poly-silicon" or "polycrystalline silicon" or "polycrystalline Si")) with (LPCVD or "low pressure chemical vapor deposition" or "low pressure CVD" or "low pressure thermal CVD"))	USPAT; US-PGPUB	2002/11/06 21:15



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☒ L1: (1) ("5895948").PN.  
☒ L2: (22402) "a-Si" or "a-silicon" or "amorphous Si" or "amorphous silicon"  
☒ L3: (0) 1 and 2  
☒ L4: (1) ("5073516").PN.  
☒ L5: (1) 2 and 4  
☒ L6: (1) ("6030894").PN.  
☒ L7: (0) 2 and 6  
☒ L8: (213378) poly or polysilicon or "poly-Si" or "poly-silicon" or "polycrystalline silicon"...  
☒ L9: (1) 6 and 8  
☒ L10: (9147) LPCVD  
☒ L11: (0) 6 and 10  
☒ L12: (2558) 2 and 10  
☒ L13: (184) (438/677).CCLS.  
☒ L14: (21) 10 and 13  
☒ L15: (12693) LPCVD or "low pressure chemical vapor deposition" or "low pressure CVD" or "low...  
☒ L16: (0) 4 and 15  
☒ L17: (257) UHVCD or "ultra high vacuum chemical vapor deposition" or "ultra-high vacuum chem...  
☒ L18: (0) 4 and 17  
☒ L19: (3056) SEG or "selective epitaxial growth"  
☒ L20: (30) 15 with 19  
☒ L21: (7253) 2 with 8  
☒ L22: (0) 20 with 21  
☒ L23: (0) 20 same 21  
☒ L24: (3) 20 and 21

☒ Failed

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☒ Hg ☒ Details ☒ HTML

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